

REPETITIVE AVALANCHE AND dv/dt RATED

HEXFET® TRANSISTOR

IRHF9230
JANSR2N7390
[REF: MIL-PRF-19500/630]
P-CHANNEL
RAD HARD

-200 Volt, 0.80W, RAD HARD HEXFET

International Rectifier's P-Channel RAD HARD technology HEXFETs demonstrate excellent threshold voltage stability and breakdown voltage stability at total radiation doses as high as 10^5 Rads (Si). Under **identical** pre- and post-radiation test conditions, International Rectifier's P-Channel RAD HARD HEXFETs retain **identical** electrical specifications up to 1×10^5 Rads (Si) total dose. No compensation in gate drive circuitry is required. These devices are also capable of surviving transient ionization pulses as high as 1×10^{12} Rads (Si)/Sec, and return to normal operation within a few micro-seconds. Single Event Effect (SEE) testing of International Rectifier P-Channel RAD HARD HEXFETs has demonstrated virtual immunity to SEE failure. Since the P-Channel RAD HARD process utilizes International Rectifier's patented HEXFET technology, the user can expect the highest quality and reliability in the industry.

P-Channel RAD HARD HEXFET transistors also feature all of the well-established advantages of MOSFETs, such as voltage control, very fast switching, ease of paralleling and temperature stability of the electrical parameters. They are well-suited for applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high-energy pulse circuits in space and weapons environments.

Absolute Maximum Ratings

	Parameter	IRHF9230	Units
I_D @ $V_{GS} = -12V$, $T_C = 25^\circ C$	Continuous Drain Current	-4.0	A
I_D @ $V_{GS} = -12V$, $T_C = 100^\circ C$	Continuous Drain Current	-2.4	
I_{DM}	Pulsed Drain Current ①	-16	
P_D @ $T_C = 25^\circ C$	Max. Power Dissipation	25	W
	Linear Derating Factor	2.0	W/ $^\circ C$
V_{GS}	Gate-to-Source Voltage	± 20	V
EAS	Single Pulse Avalanche Energy ②	171	mJ
I_{AR}	Avalanche Current ①	-4.0	A
EAR	Repetitive Avalanche Energy ①	2.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-27	V/ns
T_J	Operating Junction	-55 to 150	$^\circ C$
T_{STG}	Storage Temperature Range		
	Lead Temperature	300 (0.063 in. (1.6mm) from case for 10s)	
	Weight	0.98 (typical)	g

Product Summary

Part Number	BV_{DSS}	$R_{DS(on)}$	I_D
IRHF9230	-200V	0.80W	-4.0A

Features:

- Radiation Hardened up to 1×10^5 Rads (Si)
- Single Event Burnout (SEB) Hardened
- Single Event Gate Rupture (SEGR) Hardened
- Gamma Dot (Flash X-Ray) Hardened
- Neutron Tolerant
- Identical Pre- and Post-Electrical Test Conditions
- Repetitive Avalanche Rating
- Dynamic dv/dt Rating
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed

Pre-Irradiation

Electrical Characteristics @ $T_j = 25^\circ\text{C}$ (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions	
BV _{DSS}	Drain-to-Source Breakdown Voltage	-200	—	—	V	V _{GS} = 0 V, I _D = -1.0mA	
DBV _{DSS} /DT _J	Temperature Coefficient of Breakdown Voltage	—	-0.25	—	V/°C	Reference to 25°C, I _D = -1.0mA	
R _{DS(on)}	Static Drain-to-Source	—	—	0.80	W	V _{GS} = -12V, I _D = -2.4A ④	
	On-State Resistance	—	—	0.92		V _{GS} = -12V, I _D = -4.0A	
V _{GS(th)}	Gate Threshold Voltage	-2.0	—	-4.0	V	V _D S = V _G S, I _D = -1.0mA	
g _{fs}	Forward Transconductance	2.5	—	—	S (M)	V _D S > -15V, I _D S = -4.0A ④	
I _{DSS}	Zero Gate Voltage Drain Current	—	—	-25	mA	V _D S= 0.8 x Max Rating, V _G S=0V	
		—	—	-250		V _D S = 0.8 x Max Rating V _G S = 0V, T _J = 125°C	
I _{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	V _G S = -20V	
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	100		V _G S = 20V	
Q _g	Total Gate Charge	—	—	45	nC	V _G S = -12V, I _D = -4.0A	
Q _{gs}	Gate-to-Source Charge	—	—	10		V _D S = Max Rating x 0.5	
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	25			
t _{d(on)}	Turn-On Delay Time	—	—	30	ns	V _D D = -50V, I _D = -4.0A, R _G = 7.5W	
t _r	Rise Time	—	—	30			
t _{d(off)}	Turn-Off Delay Time	—	—	75			
t _f	Fall Time	—	—	65			
L _D	Internal Drain Inductance	—	5.0	—	nH	Measured from drain lead, 6mm (0.25 in) from package to center of die.	Modified MOSFET symbol showing the internal inductances. 
L _S	Internal Source Inductance	—	15	—		Measured from source lead, 6mm (0.25 in) from package to source bonding pad.	
C _{iss}	Input Capacitance	—	1200	—	pF	V _G S = 0V, V _D S = -25V f = 1.0MHz	
C _{oss}	Output Capacitance	—	190	—			
C _{rss}	Reverse Transfer Capacitance	—	45	—			

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-4.0	A	Modified MOSFET symbol showing the integral reverse p-n junction rectifier. 
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	-16		
V _{SD}	Diode Forward Voltage	—	—	-5.0	V	T _J = 25°C, I _S = -4.0A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	—	400	ns	T _J = 25°C, I _F = -4.0A, di/dt £ -100A/ms V _{DD} £ -100V ④
Q _{RR}	Reverse Recovery Charge	—	—	1.6	mC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	5.0	°C/W	
R _{thJA}	Junction-to-Ambient	—	175	—		Typical socket mount

Radiation Performance of P-Channel Rad Hard HEXFETs

International Rectifier Radiation Hardened HEXFETs are tested to verify their hardness capability. The hardness assurance program at International Rectifier comprises three radiation environments.

Every manufacturing lot is tested in a low dose rate (total dose) environment per MIL-STD-750, test method 1019 condition A. International Rectifier has imposed a standard gate condition of -12 volts per note 5 and a V_{DS} bias condition equal to 80% of the device rated voltage per note 6. Pre- and post- irradiation limits of the devices irradiated to 1×10^5 Rads (Si) are identical and are presented in Table 1, column 1, IRHF9230. The values in Table 1 will be met for either of the two low dose rate test circuits that are used. Both pre- and

post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

High dose rate testing may be done on a special request basis using a dose rate up to 1×10^{12} Rads (Si)/Sec (See Table 2).

International Rectifier radiation hardened P-Channel HEXFETs are considered to be neutron-tolerant, as stated in MIL-PRF-19500 Group D. International Rectifier radiation hardened P-Channel HEXFETs have been characterized in heavy ion Single Event Effects (SEE) environments. Single Event Effects characterization is shown in Table 3.

Table 1. Low Dose Rate ⑤ ⑥

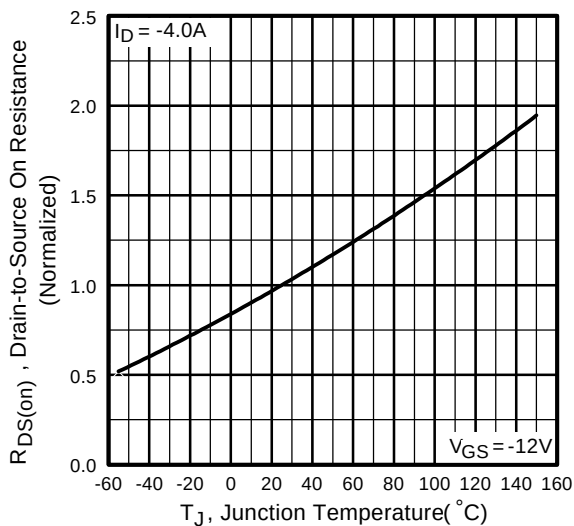
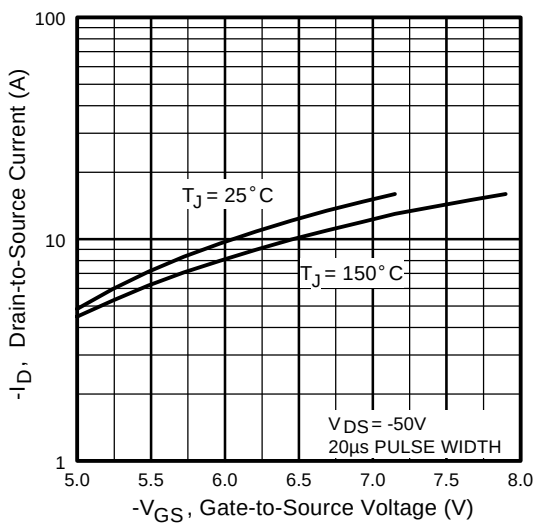
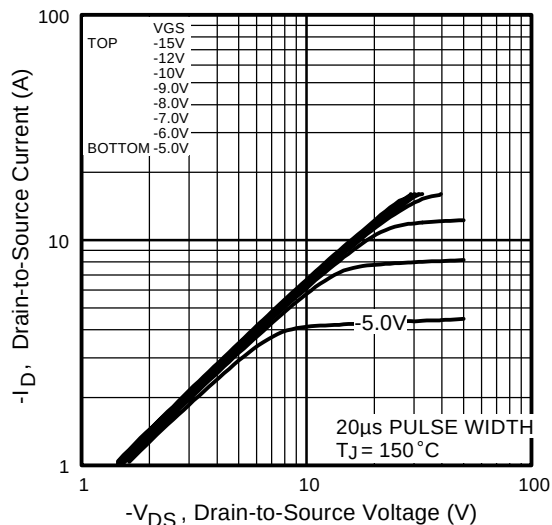
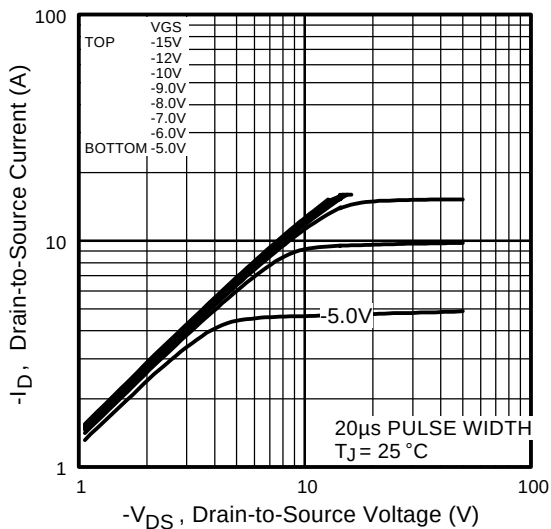
Table 1. Low Dose Rate ⑤ ⑥		IRHF9230		Units	Test Conditions ⑧
	Parameter	100K Rads (Si)			
		Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	-200	—	V	V _{GS} = 0V, I _D = -1.0mA
V _{GS(th)}	Gate Threshold Voltage ④	-2.0	-4.0		V _{GS} = V _{DS} , I _D = -1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	-100	nA	V _{GS} = -20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	100		V _{GS} = 20V
I _{DSS}	Zero Gate Voltage Drain Current	—	-25	μA	V _{DS} =0.8 x Max Rating, V _{GS} =0V
R _{DS(on)1}	Static Drain-to-Source ④	—	0.8	W	V _{GS} = -12V, I _D =-2.4A
	On-State Resistance One				
V _{SD}	Diode Forward Voltage ④	—	-5.0	V	T _C = 25°C, I _S = -4.0A,V _{GS} = 0V

Table 2. High Dose Rate ⑦

	Parameter	10^{11} Rads (Si)/sec			10^{12} Rads (Si)/sec			Units	Test Conditions
		Min	Typ	Max	Min	Typ	Max		
V_{DSS}	Drain-to-Source Voltage	—	—	-160	—	—	-160	V	Applied drain-to-source voltage during gamma-dot
I_{pp}		—	-100	—	—	-100	—	A	Peak radiation induced photo-current
di/dt		—	—	-800	—	—	-160	A/ μ sec	Rate of rise of photo-current
L_1		27	—	—	0.5	—	—	μH	Circuit inductance required to limit di/dt

Table 3. Single Event Effects

Ion	LET (Si) (MeV/mg/cm ²)	Fluence (ions/cm ²)	Range (μm)	V_{DS} Bias (V)	V_{GS} Bias (V)
Cu	28	3×10^5	~43	-200	5



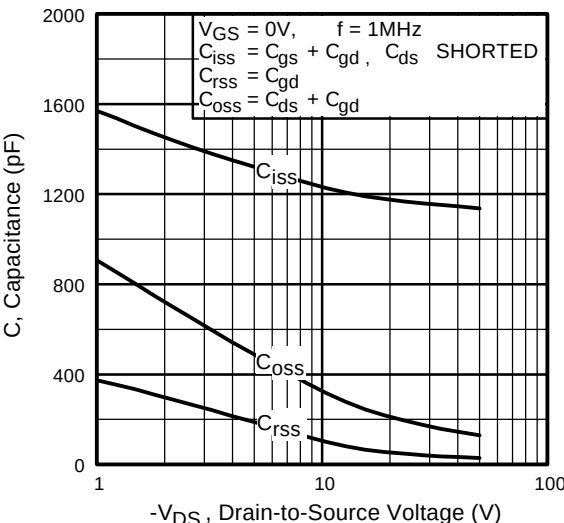


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

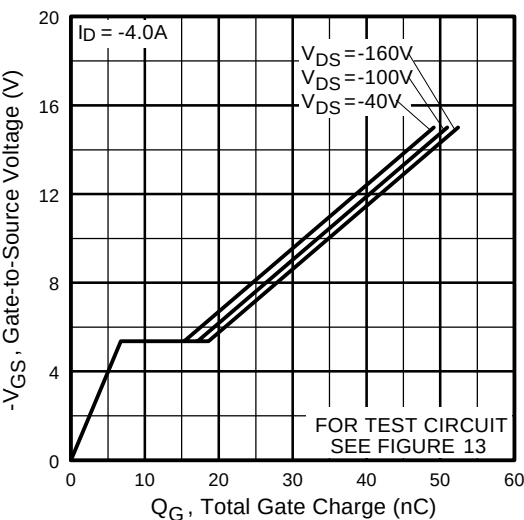


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

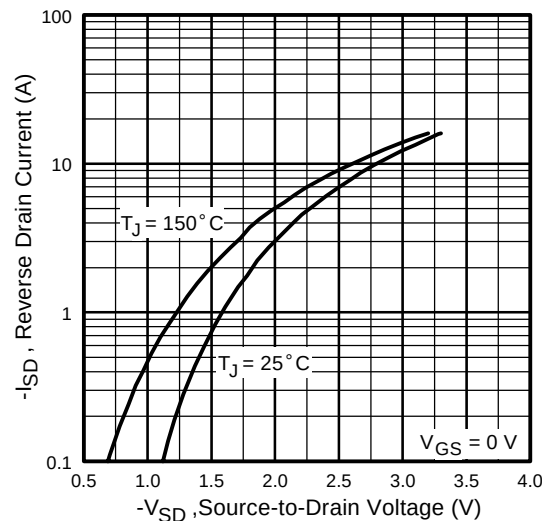


Fig 7. Typical Source-Drain Diode Forward Voltage

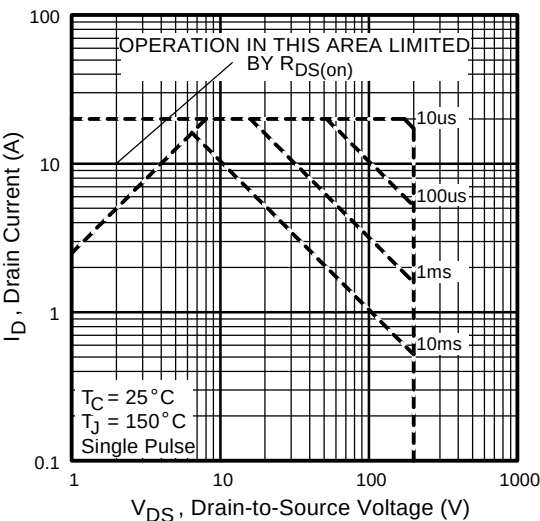


Fig 8. Maximum Safe Operating Area

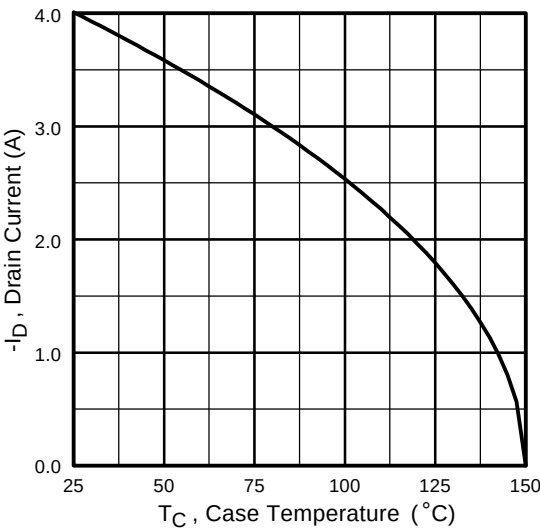


Fig 9. Maximum Drain Current Vs. Case Temperature

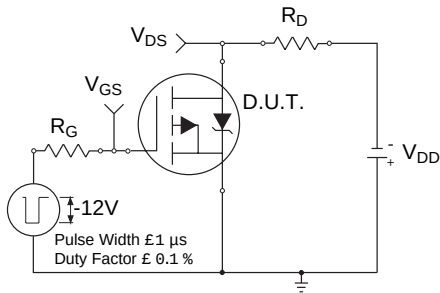


Fig 10a. Switching Time Test Circuit

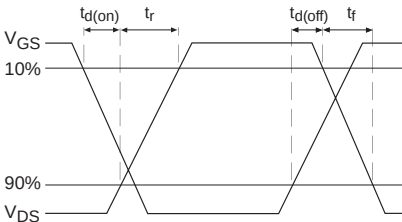


Fig 10b. Switching Time Waveforms

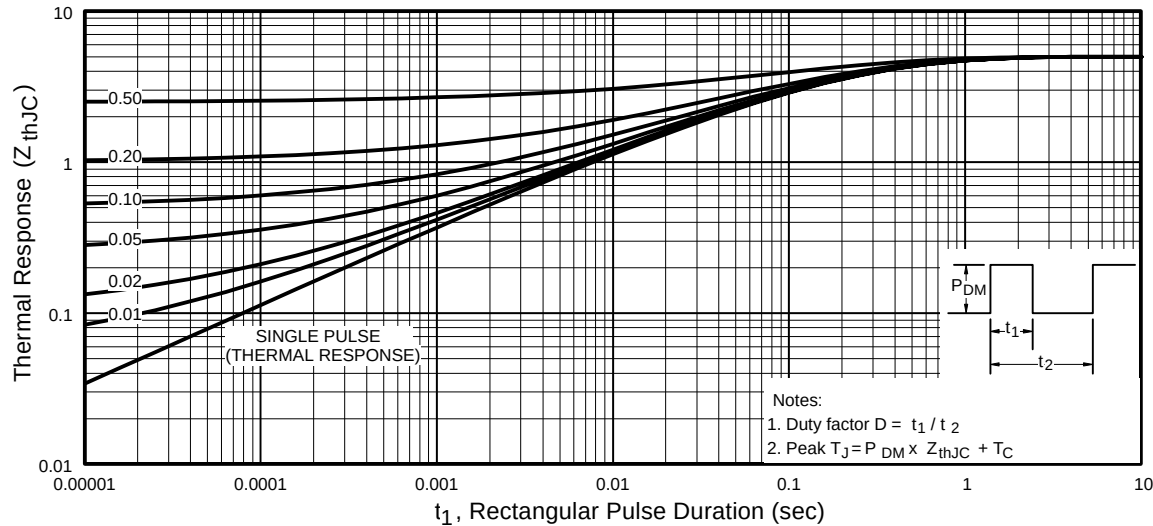


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

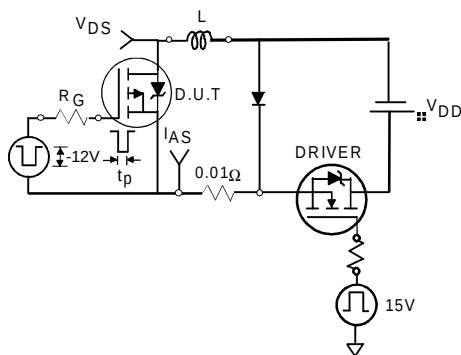


Fig 12a. Unclamped Inductive Test Circuit

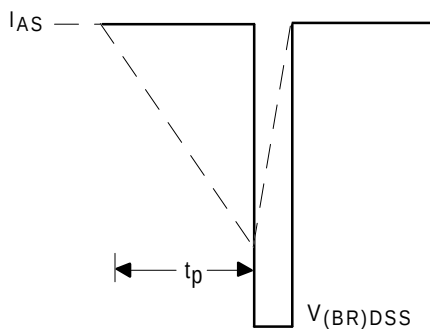


Fig 12b. Unclamped Inductive Waveforms

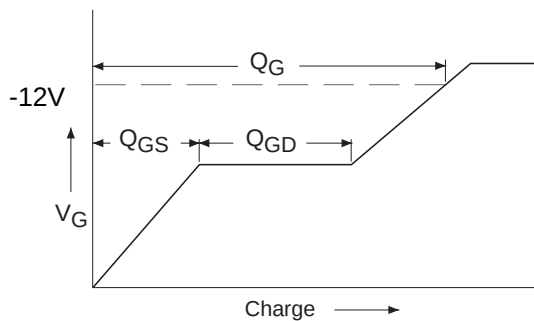


Fig 13a. Basic Gate Charge Waveform

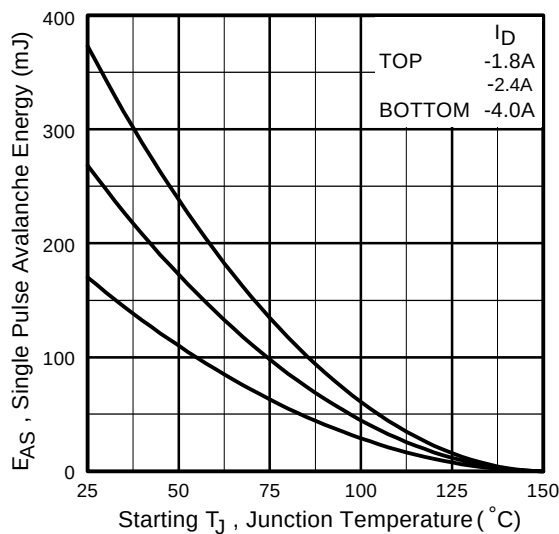


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

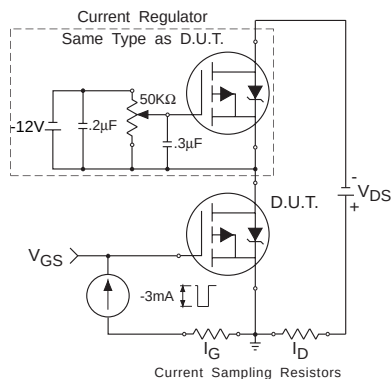
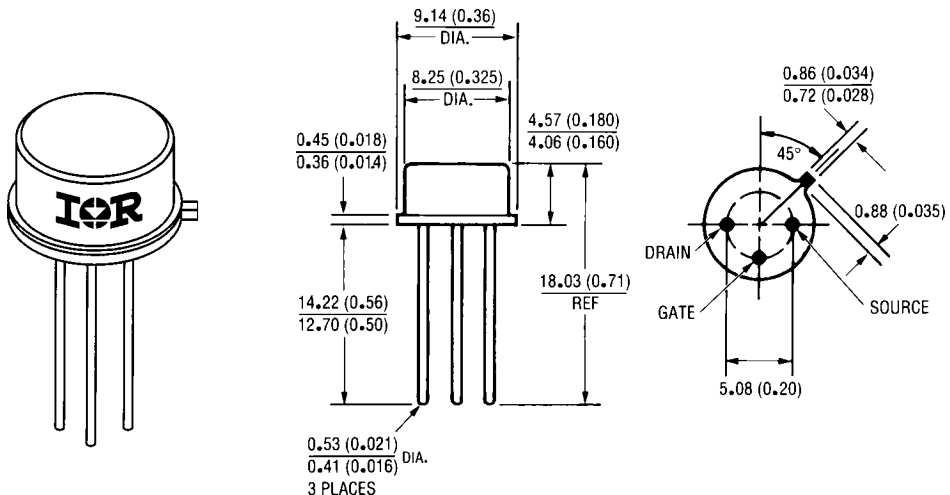


Fig 13b. Gate Charge Test Circuit

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
Refer to current HEXFET reliability report.
- ② @ $V_{DD} = -50V$, Starting $T_J = 25^\circ C$,
 $EAS = [0.5 * L * (I_L^2)]$
Peak $I_L = -4.0A$, $V_{GS} = -12V$, $25 \leq R_G \leq 200\Omega$
- ③ $ISD \leq -4.0A$, $di/dt \leq -150A/ms$,
 $V_{DD} \leq BV_{DSS}$, $T_J \leq 150^\circ C$
Suggested $R_G = 7.5\Omega$
- ④ Pulse width $\leq 300 ms$; Duty Cycle $\leq 2\%$
- ⑤ **Total Dose Irradiation with V_{GS} Bias.**
-12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019.
- ⑥ **Total Dose Irradiation with V_{DS} Bias.**
 $V_{DS} = 0.8$ rated BV_{DSS} (pre-radiation) applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019.
- ⑦ This test is performed using a flash x-ray source operated in the e-beam mode (energy $\sim 2.5 MeV$), 30 nsec pulse.
- ⑧ All Pre-Radiation and Post-Radiation test conditions are **identical** to facilitate direct comparison for circuit applications.

Case Outline and Dimensions — TO-205AF (Modified TO-39)



All dimensions are shown millimeters (inches)

International
IOR Rectifier

WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, Tel: (310) 322 3331

IR GREAT BRITAIN: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR FAR EAST: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo Japan 171 Tel: 81 3 3983 0086

IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 838 4630

IR TAIWAN: 16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673, Taiwan Tel: 886-2-2377-9936

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